AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (original) A method for producing a substrate having a crystalline Si layer comprising the steps of forming an amorphous Si layer on a plastic substrate, and irradiating said amorphous Si layer with a laser beam to crystallize said amorphous Si, wherein said plastic substrate has light transmittance of 30 to 100% at an oscillation wavelength of said laser beam.

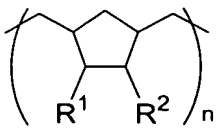
2. (original): The method of claim 1 for producing a substrate having a crystalline Si layer, wherein said amorphous Si layer has a thickness of 1 to 2000 nm.

3. (currently amended): The method of claim 1 ~~or 2~~ for producing a substrate having a crystalline Si layer, wherein the oscillation wavelength of said laser beam is 140 to 450 nm.

4. (currently amended): The method of ~~any one of claims 1 to 3~~claim 1 for producing a substrate having a crystalline Si layer, wherein said laser is an excimer laser.

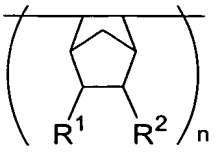
5. (currently amended): The method of ~~any one of claims 1 to 4~~claim 1 for producing a substrate having a crystalline Si layer, wherein said plastic substrate is made of amorphous polyolefin or polyethersulfone.

6. (currently amended): The method of ~~any one of claims 1 to 5~~claim 1 for producing a substrate having a crystalline Si layer, wherein said plastic substrate is made of a cycloolefin polymer represented by the following general formula (1):



... (1),

or by the following general formula (2):



... (2),

wherein R^1 and R^2 independently represent a hydrogen atom, a nonpolar group, a halogen atom, a hydroxyl group, an ester group, an alkoxy group, a cyano group, an amide group, an imide group or a silyl group; n represents an integer of 1 to 100,000; and R^1 and R^2 may be connected to each other to form a mono- or poly-cyclic ring, provided that R^1 and R^2 do not form a 5-membered, unsubstituted, saturated, monocyclic hydrocarbon.

7. (currently amended): A substrate having a crystalline Si layer produced by the method recited in ~~any one of claims 1 to 6~~claim 1.

8. (original): The substrate of claim 7 having a crystalline Si layer, wherein said plastic substrate is provided with an insulating thin film having a thickness of 10 nm to 10 μm on at least one surface.

9. (currently amended): A crystalline Si device comprising the substrate of claim 7 ~~or 8~~ having a crystalline Si layer.